

Phonon tunneling loss solver for micro- and nanomechanical resonators

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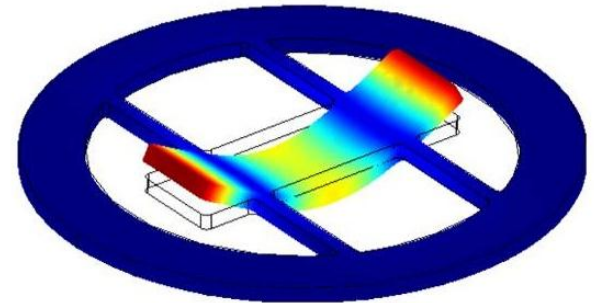
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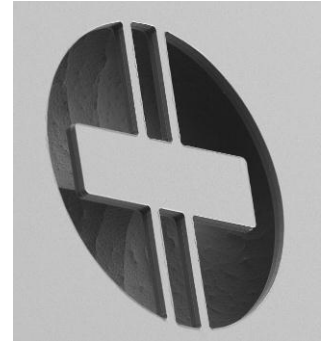
Controlling Damping in Resonators



Goal: quantitative prediction of the mechanical quality factor

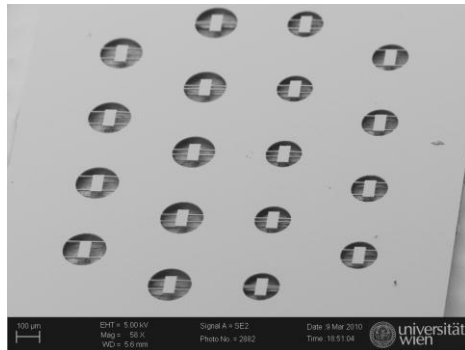
Metrology

Scanning probe and magnetic resonance force microscopy
→ *Improved imaging and smaller resolvable feature size*



Communications

Wireless filters, programmable oscillators, and on-chip clocks
→ *Low power narrowband filters and frequency references*



Fundamental Scientific Investigations

Sensitive probes for force, mass, and position measurement
→ *Single-particle sensing, operation at the quantum limit*

Approach: combine FEM-based solver with characterization of micromechanical resonators



Four key factors contribute to total dissipation

$$\frac{1}{Q_{total}} = \frac{1}{Q_{fluidic}} + \frac{1}{Q_{thermoelastic}} + \frac{1}{Q_{materials}} + \frac{1}{Q_{anchor}}$$

First two mechanisms are well understood:

1. Fluidic: results from air flow around moving structure or squeeze-film effects from trapped gases
2. Thermoelastic: strain driven thermal gradient dissipated via irreversible heat conduction



Four key factors contribute to total dissipation

$$\frac{1}{Q_{total}} = \frac{1}{Q_{fluidic}} + \frac{1}{Q_{thermoelastic}} + \frac{1}{Q_{materials}} + \frac{1}{Q_{anchor}}$$

Remaining mechanisms require further investigation:

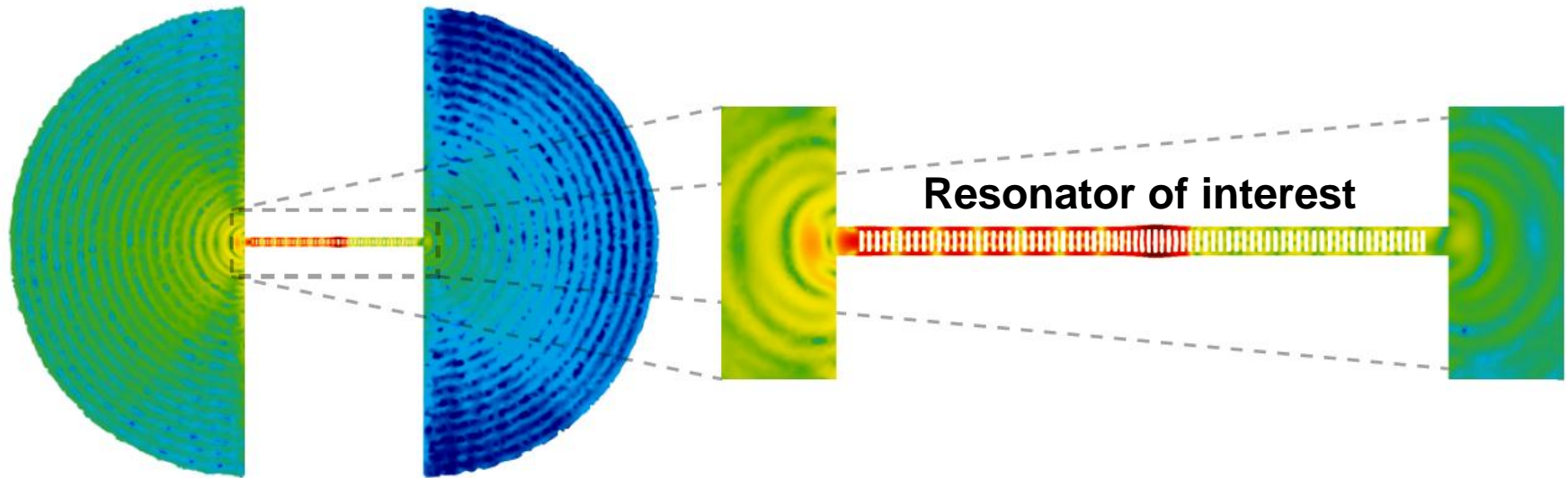
3. Materials: intrinsic to the specific microstructure, e.g. two-level fluctuators in amorphous materials (SiO_2)

4. Anchor: acoustic transmission from the resonator into the supporting medium (i.e. phonon tunneling)

Anchor Loss: Elastic Wave Transmission



Lossy contact pads

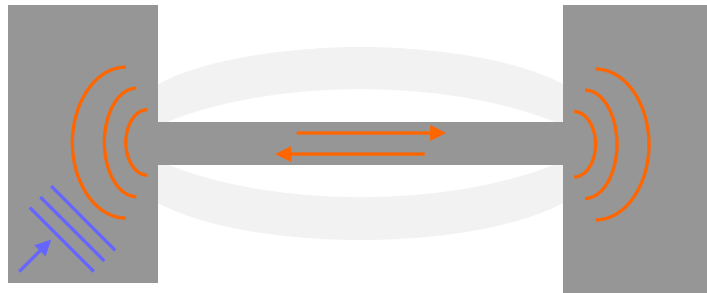


- Fundamental loss mechanism in all suspended resonator structures
 - temperature independent process; intrinsic limitation to quality factor
- Previous approaches to modeling this process are quite cumbersome
 - simulations include large contact area; artificial loss introduced to substrate
 - rigorous solution to elastic wave propagation beyond suspension points

Phonon Tunneling Concept



Mechanical Resonator (Phononic Cavity)



Optical Resonator (Photonic Cavity)



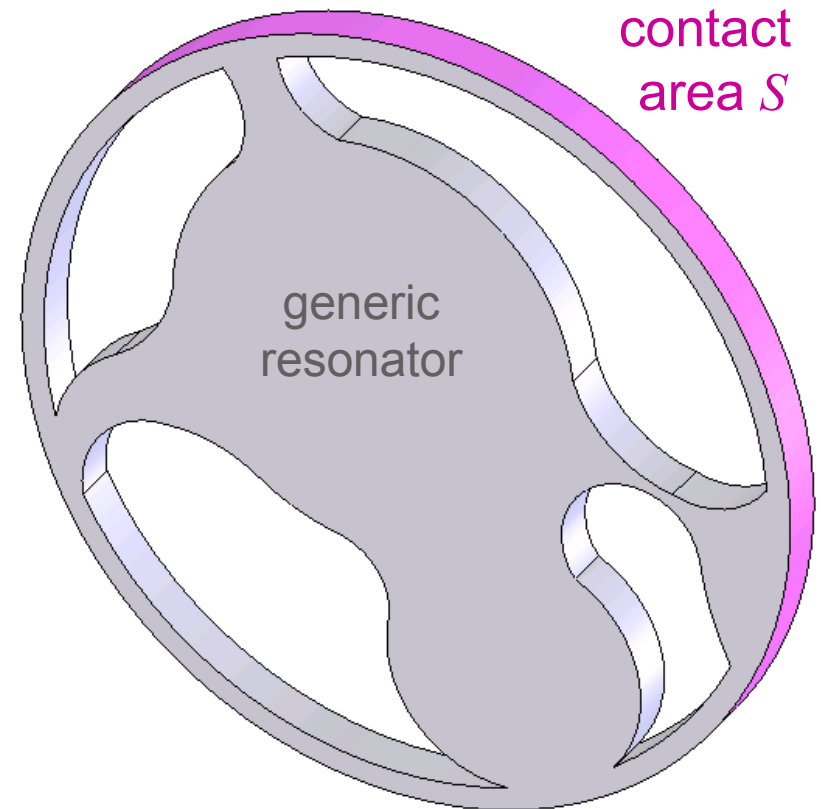
- Goal: calculate scattering modes of mechanical resonator
- Analogy: resonator as a mechanical Fabry-Perot interferometer
 - transmission and reflection of phonons at 3D-1D junction
- Resonator \rightarrow phononic waveguide: 4 branches lacking infrared cutoff
 - compression (c), torsion (t), vertical (v), and horizontal (h) bending
- Phononic modes of resonator/substrate calculated via elasticity theory
 - inverse aspect ratio (d/L) yields natural small parameter

Phonon Tunneling Q-Solver



$$\frac{1}{Q} = \frac{\pi}{2\rho_s\rho_R\omega_R^3} \int_q \left| \int_S d\bar{S} \cdot \left(\sigma_q^{(0)} \cdot \bar{u}'_R - \sigma'_R \cdot \bar{u}_q^{(0)} \right) \right|^2 \delta[\omega_R - \omega(q)]$$

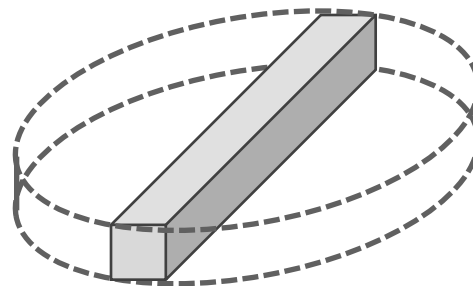
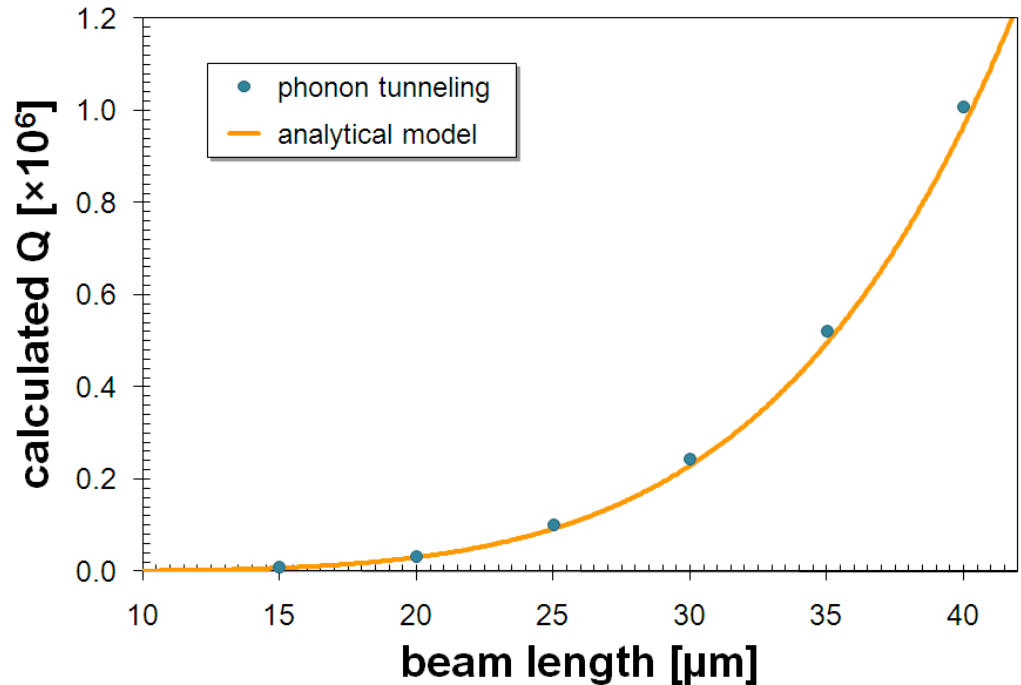
- Coupling of the free modes of the substrate and suspended resonator
 - applying Fermi's Golden Rule to phonon decay with the interaction Hamiltonian between the resonator volume and supports
- Calculation enabled by a standard eigenfrequency analysis via FEM
 - resonator mode and stress distribution via COMSOL
 - cylindrical modes assumed for support; substrate modelled as elastic half-space



Initial Verification of Numerical Solver

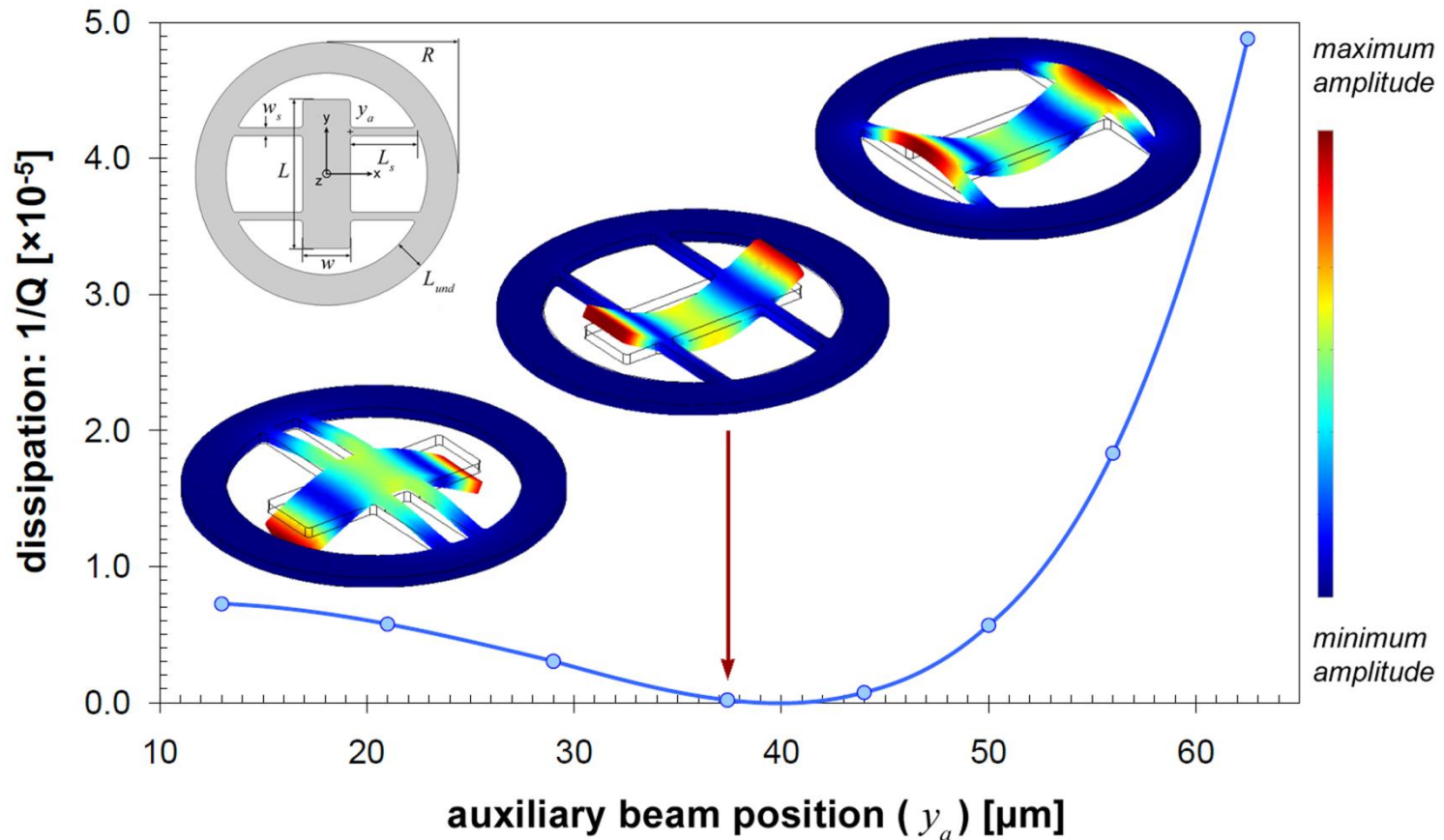


- Simple beam geometries tested to ascertain errors in numerical simulation
 - plot: results for $1 \times 1 \mu\text{m}^2$ bridges with aspect ratios from 15:1 to 40:1
- Compares well with analytical expressions developed previously
 - **FEM-derived Q values scale as length^5 for doubly-clamped beams**
 - we record a maximum error of 20% for this initial test (failure of the weak coupling approx.)



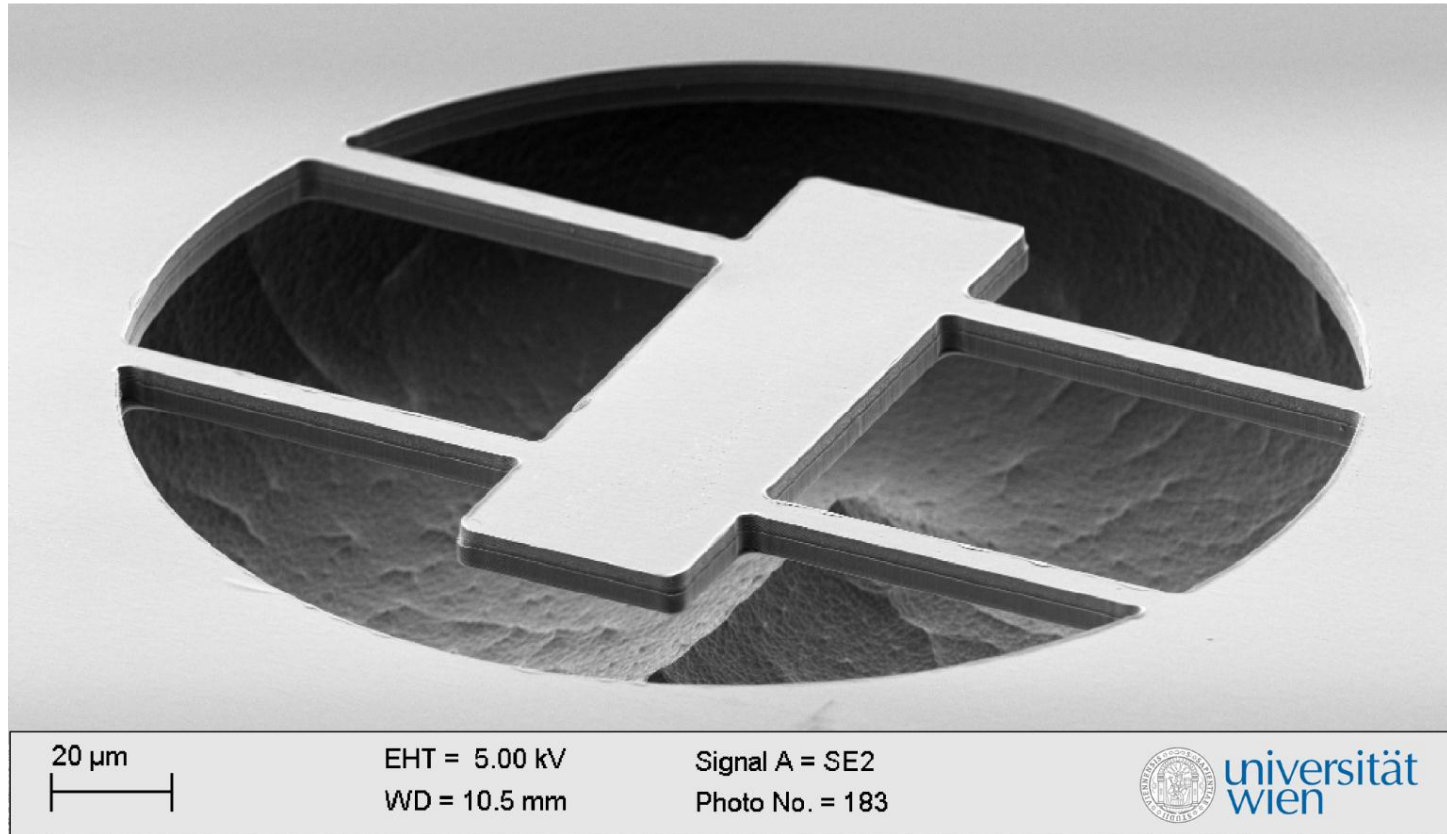
$$Q_{c-c} = \frac{0.92 L^5}{\pi^4 w t^4}$$

Experiment: Free-Free Resonators



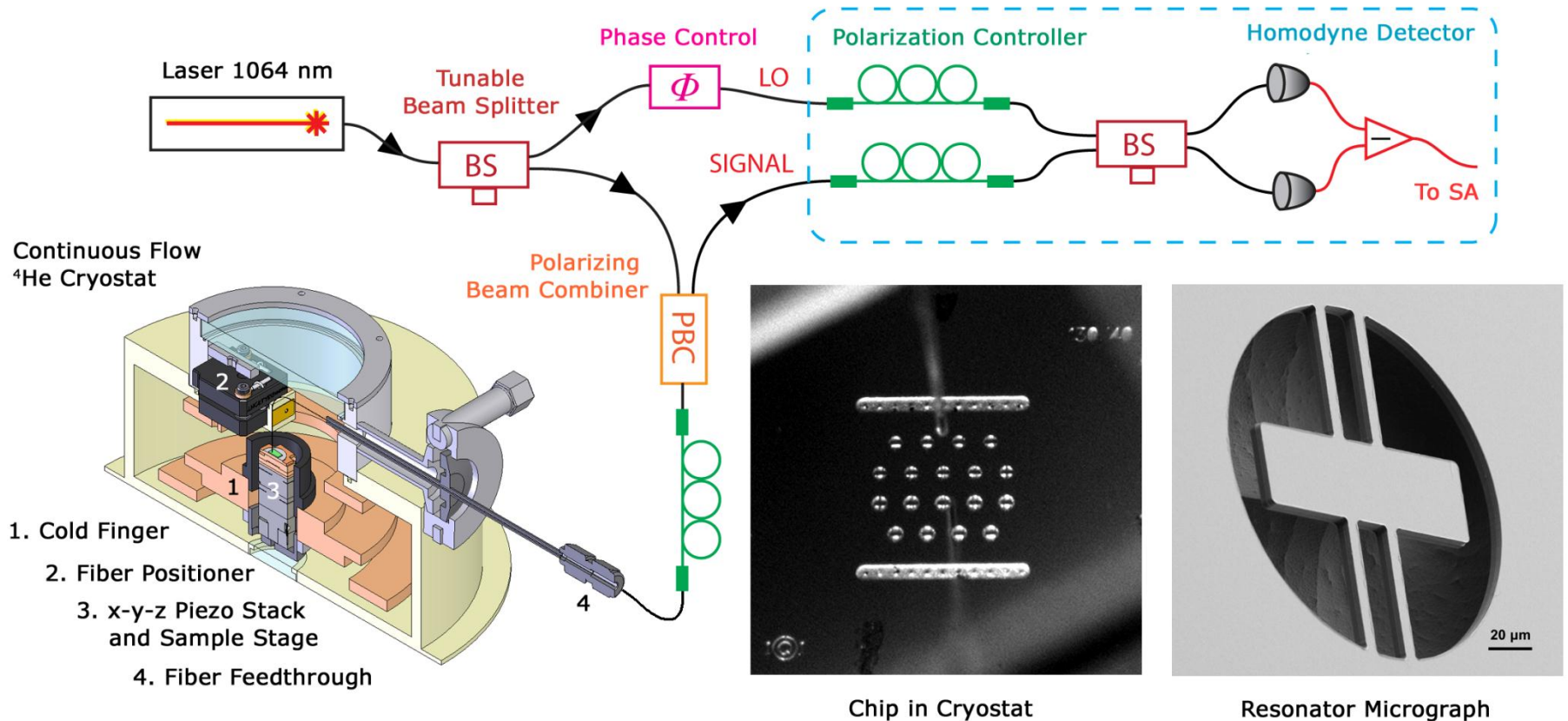
- Ideal resonator design for isolating support-induced losses
- Geometry variation with \sim constant frequency & surface-to-volume ratio

Fabricated Free-Free Resonator



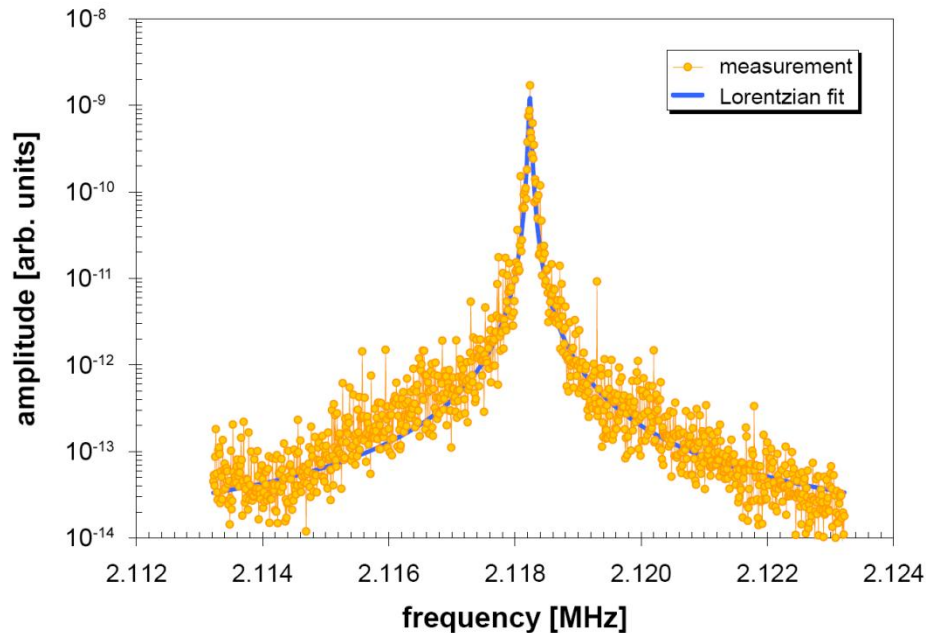
- Single-mask bulk micromachining process, excellent geometric control
- XeF_2 provides near infinite selectivity in Ge etch over GaAs/AlAs DBR

Cryogenic Optical Fiber Interferometer

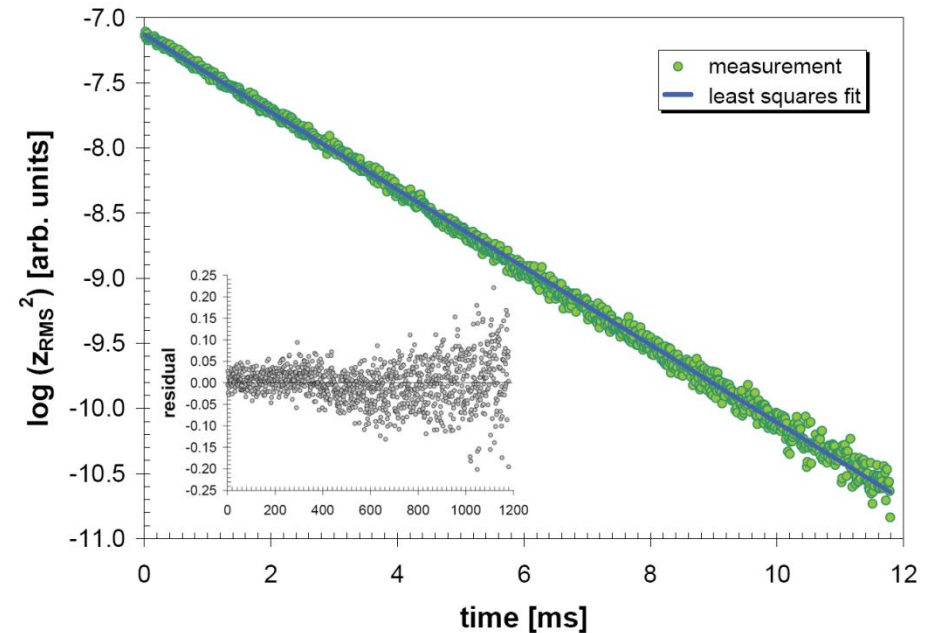


- Operation from 300 K to 20 K (4 K possible with radiation shielding)
- Turbo-pump equipped for high-vacuum operation (2.5×10^{-7} millibar)

Resonance

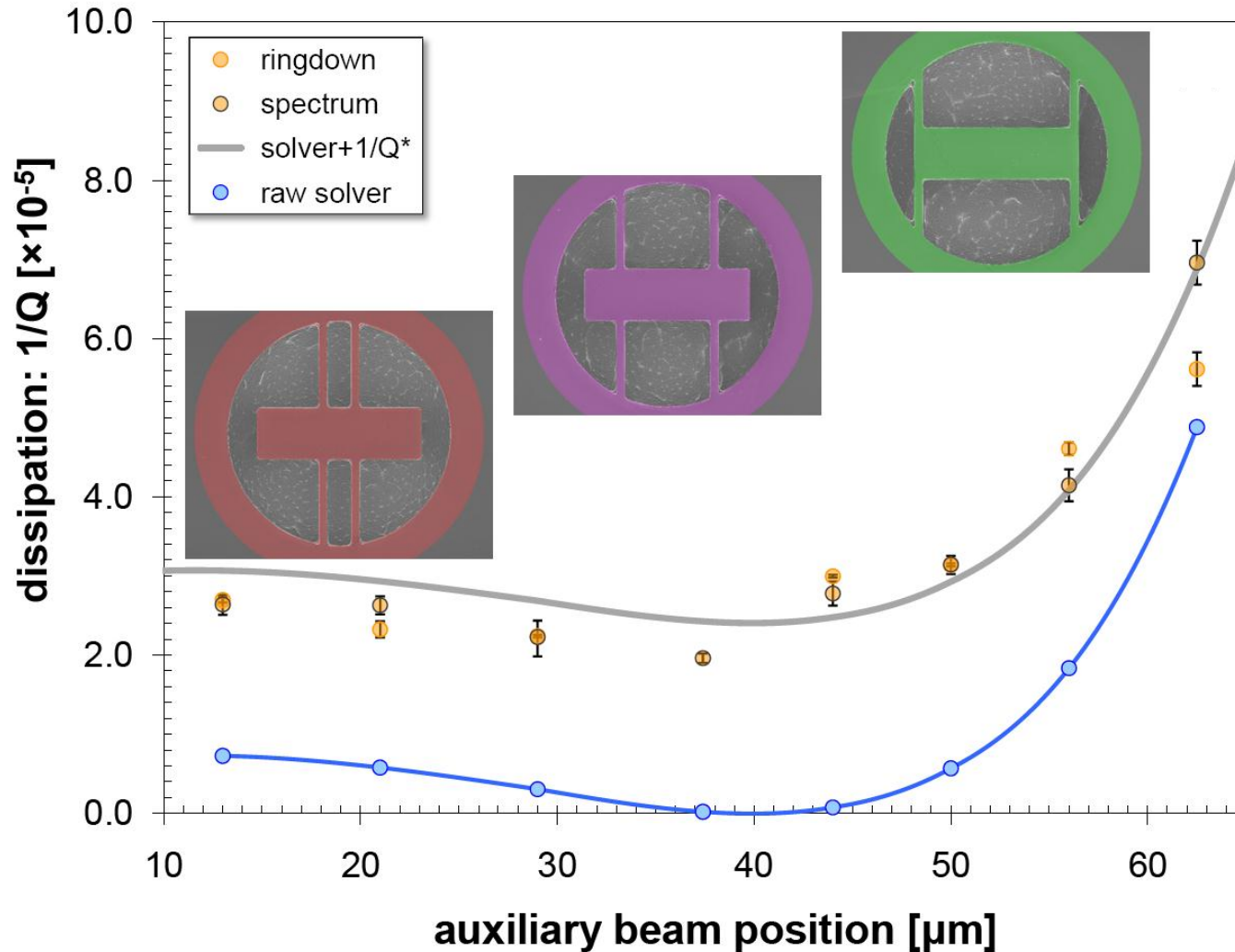


Ringdown



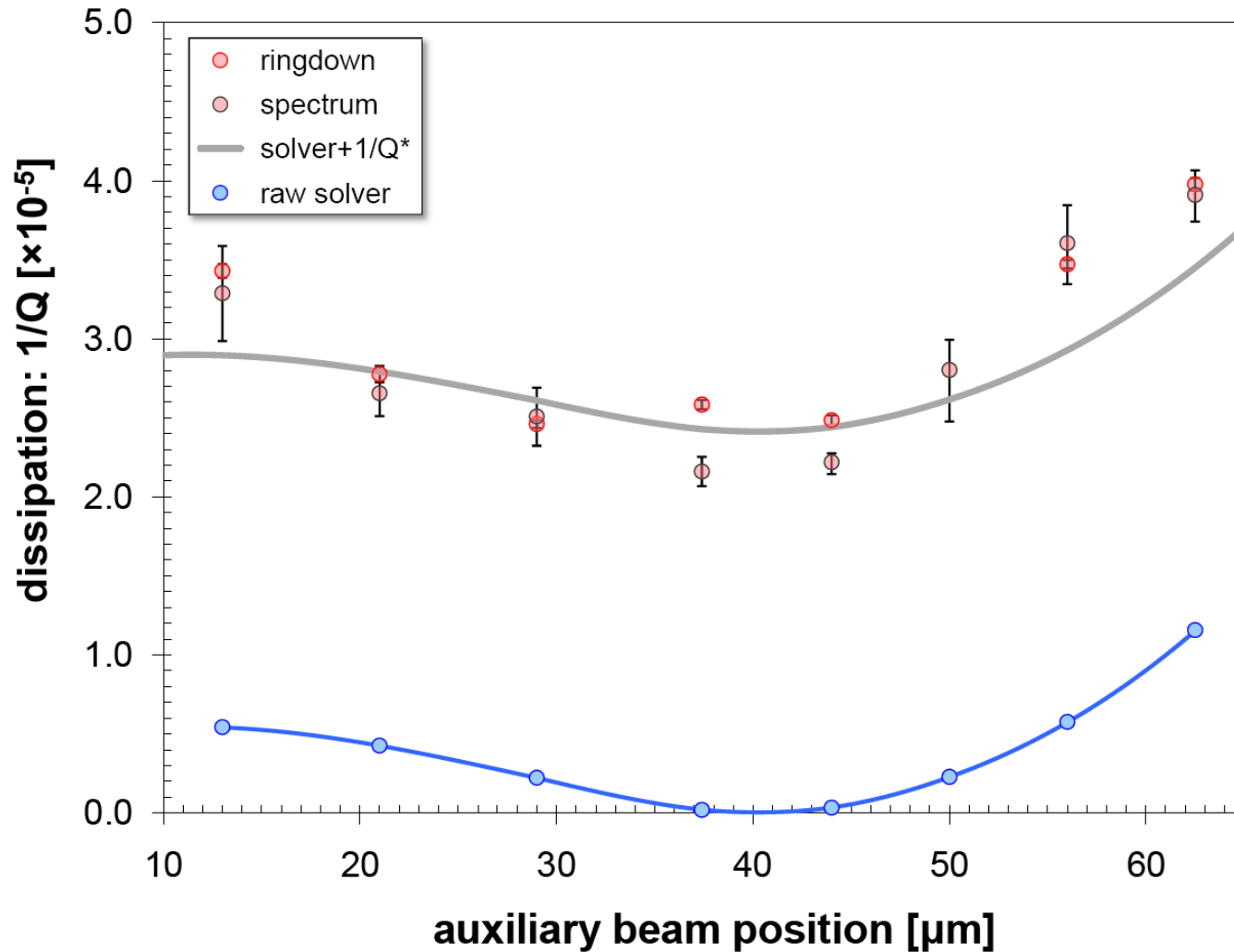
- Two methods for Q determination: white noise and resonant driving
 - white noise excites all modes simultaneously, Lorentzian fitting for Q
 - coherent drive and cessation for free-ringdown response, exponential fit

Compiled Results: $R = 116 \mu\text{m}$



- Inset images: micrographs of resonators with CAD overlay
- Simultaneously fitting all devices
 - both radii (x 2)
 - two chips
- Free parameter
 - $1/Q^*$ (offset) for background dissipation

Compiled Results: $R = 131 \mu\text{m}$

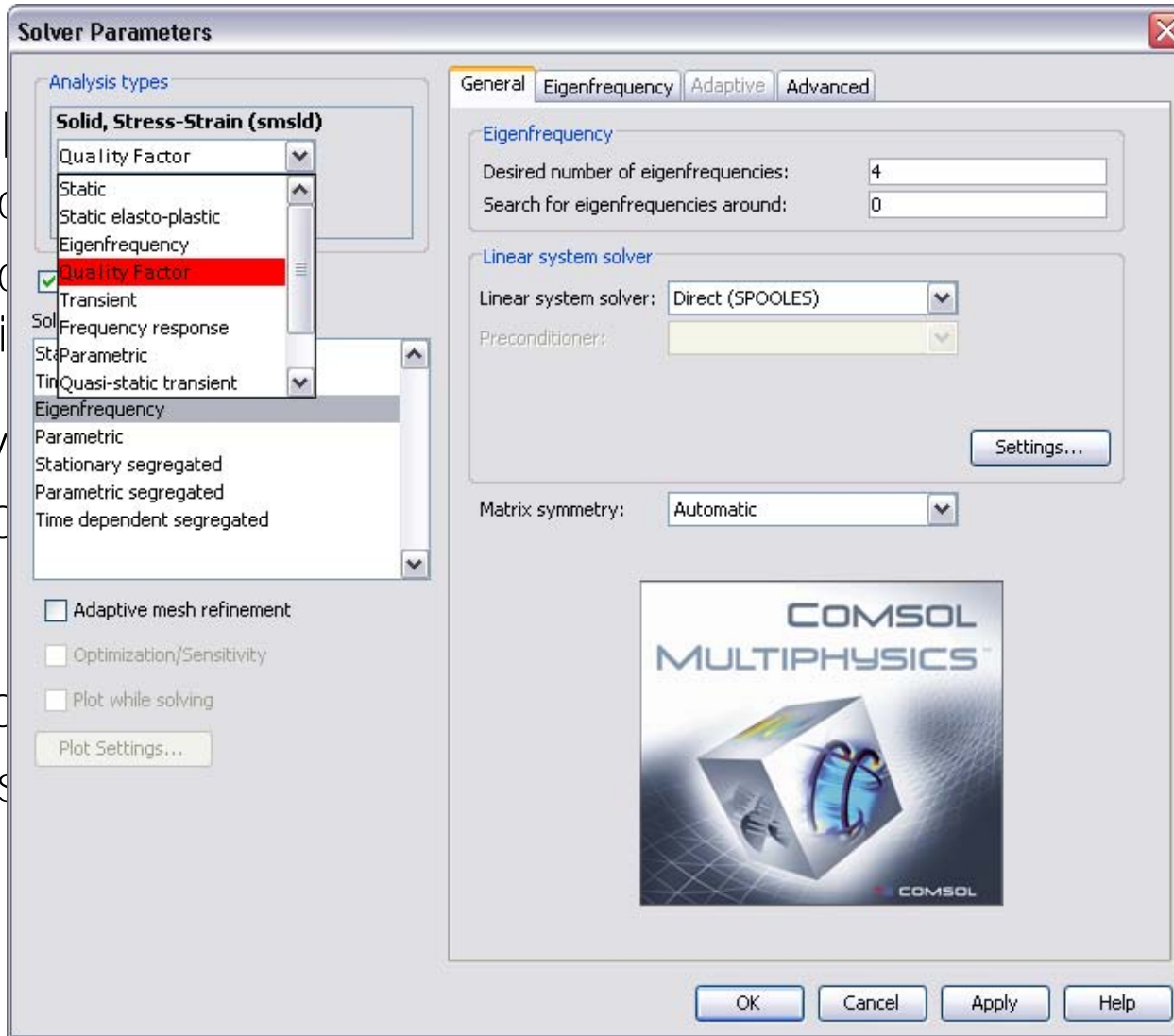


- $1/Q^*$ offset of 2.41×10^{-5} for optimal fitting
 - material related damping mech.
- Substrate props:
 - grade 2 Ti
 - E : 116 GPa
 - ρ : 4540 kg/m³
- Excellent match
 - single free parameter

Conclusions and Future Work



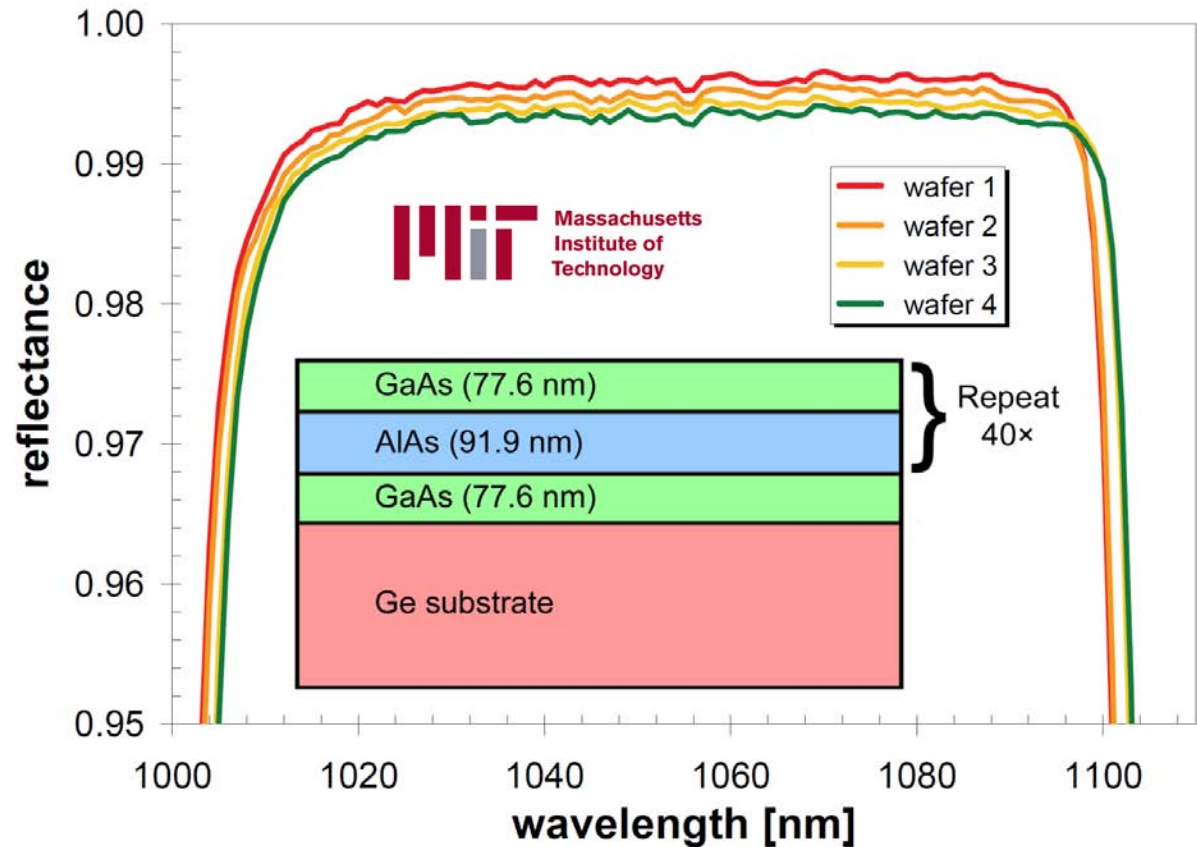
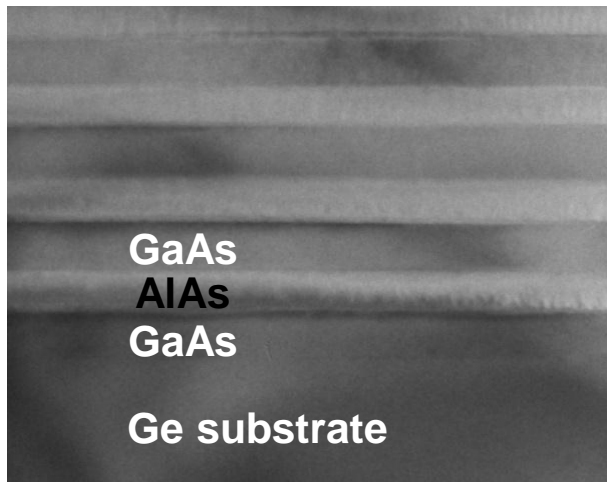
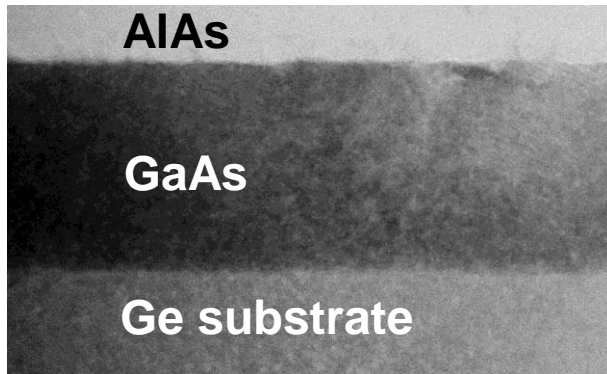
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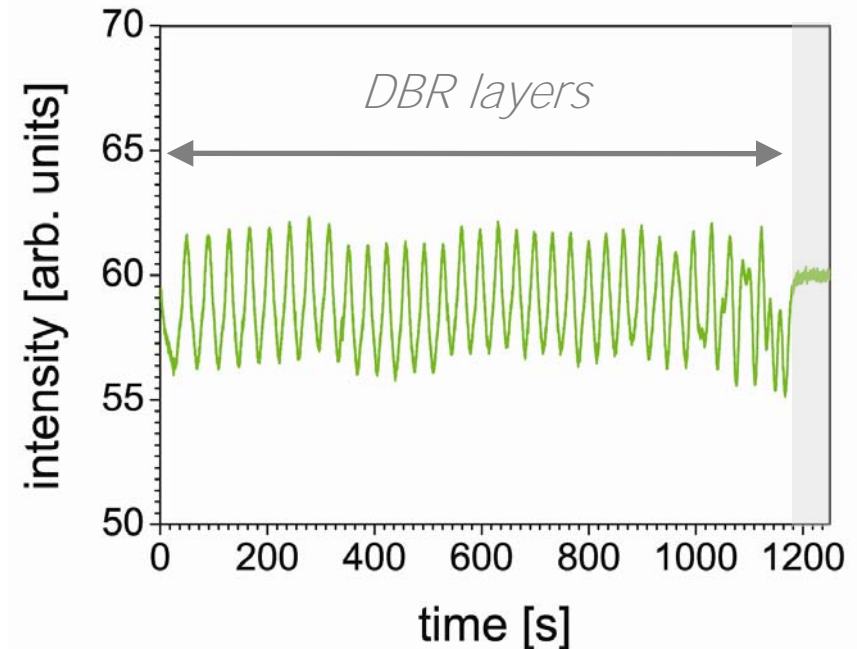
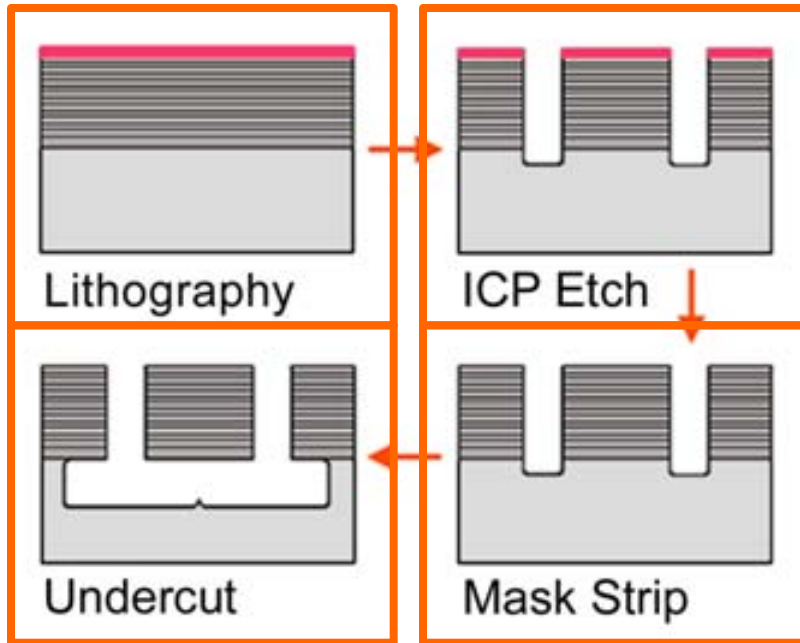


Heteroepitaxial Monocrystalline DBR



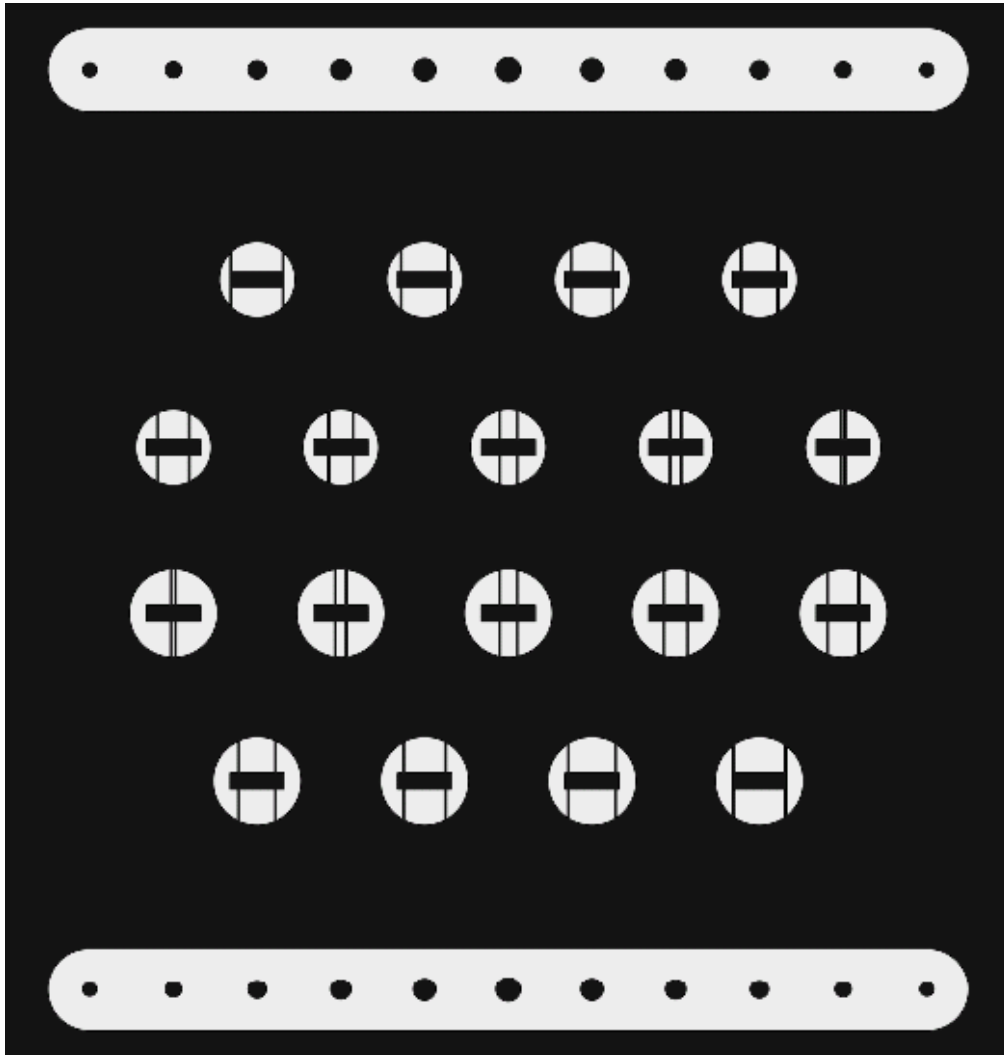
- 40-period GaAs/AlAs crystalline multilayer grown on a Ge substrate
 - Ge sacrificial material allows for increased flexibility in processing
- Surface roughness due to lattice mismatch limits reflectance (99.87%)

AlGaAs Micromirror Process Flow



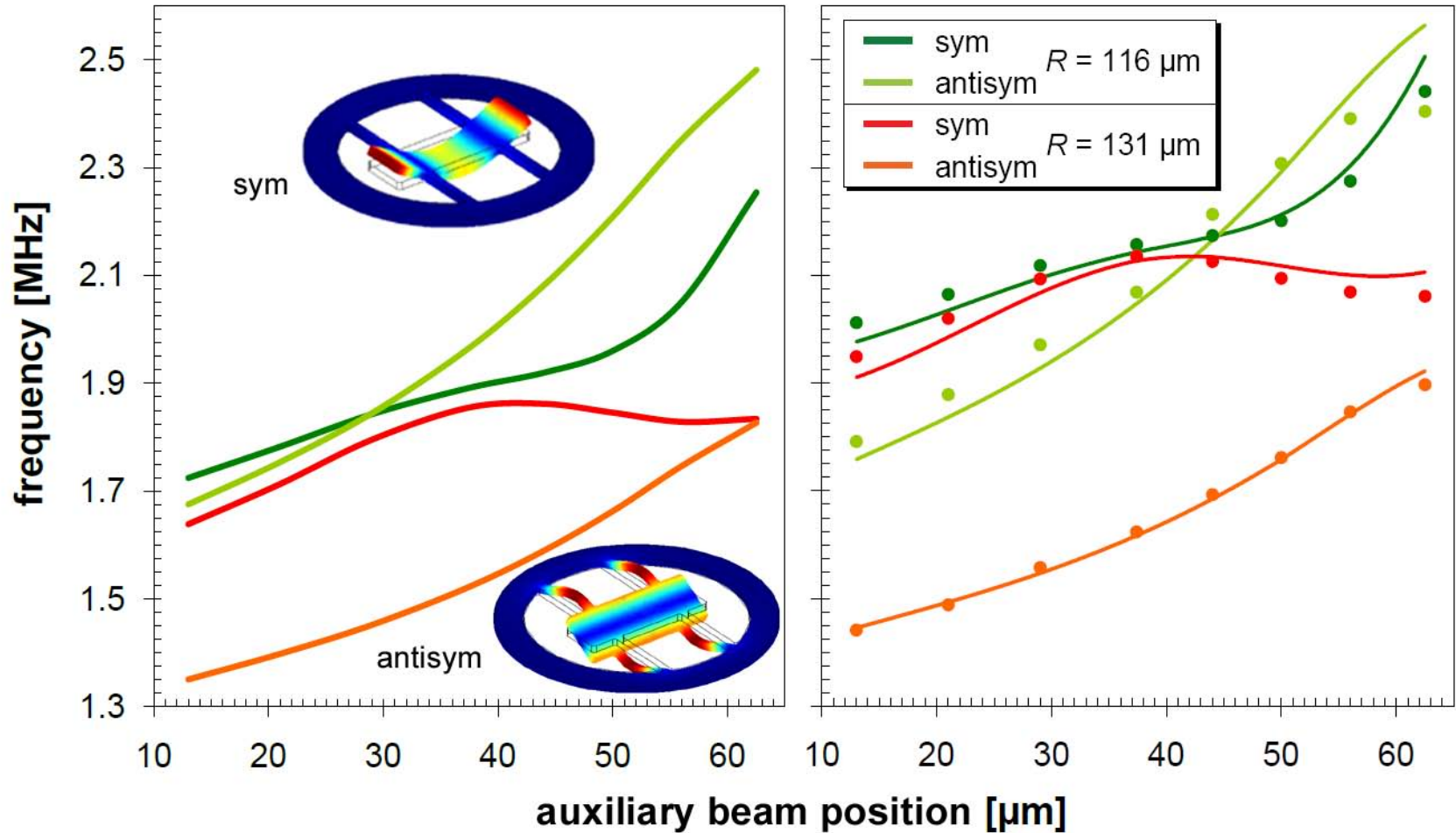
1. Resonator pattern: optical lithography with contact aligner
2. Define mechanics: SiCl_4/N_2 ion etch through DBR to Ge substrate
3. Strip masking layer: acetone and isopropanol rinse, O_2 plasma
4. Undercut: selective Ge dry etch with noble gas halide, XeF_2

Experimental Parameters



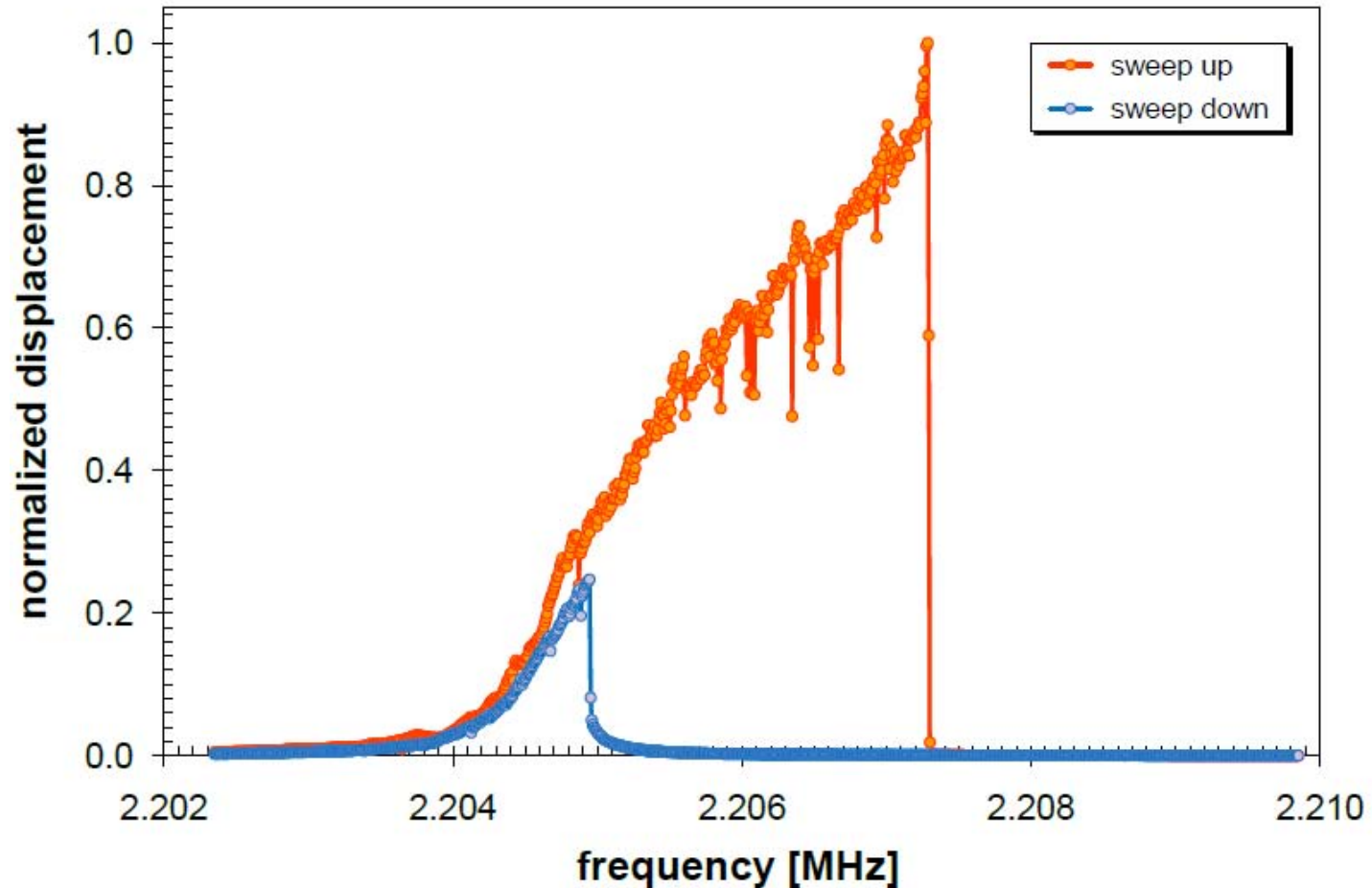
- Fixed central resonator dimensions: 130 x 40 μm
- Varying auxiliary beam attachment points (8)
 - 13, 21, 29, 37.4, 44, 50, 56, and 62.5 μm
 - aux. beams sample resonator mode shape
- Two distinct outer radii of 90 and 105 μm
 - investigate Q-variation in aux. beam length
- Undercut process monitoring structures

Mode Identification



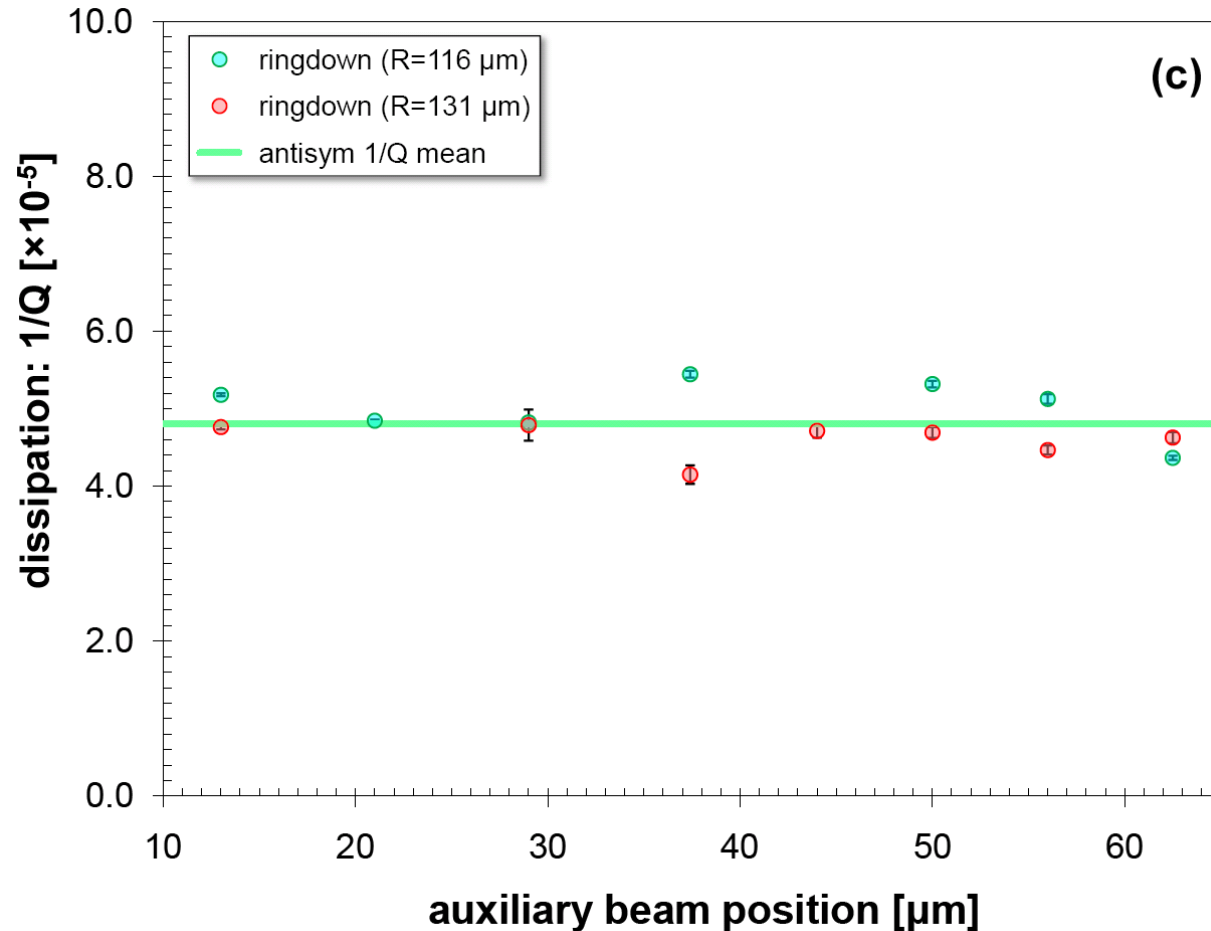
- FEM accurately captures geometric dependence of the resonances

Mode Identification



- Antisymmetric mode displays hardening-spring Duffing response

Antisymmetric Mode Dissipation

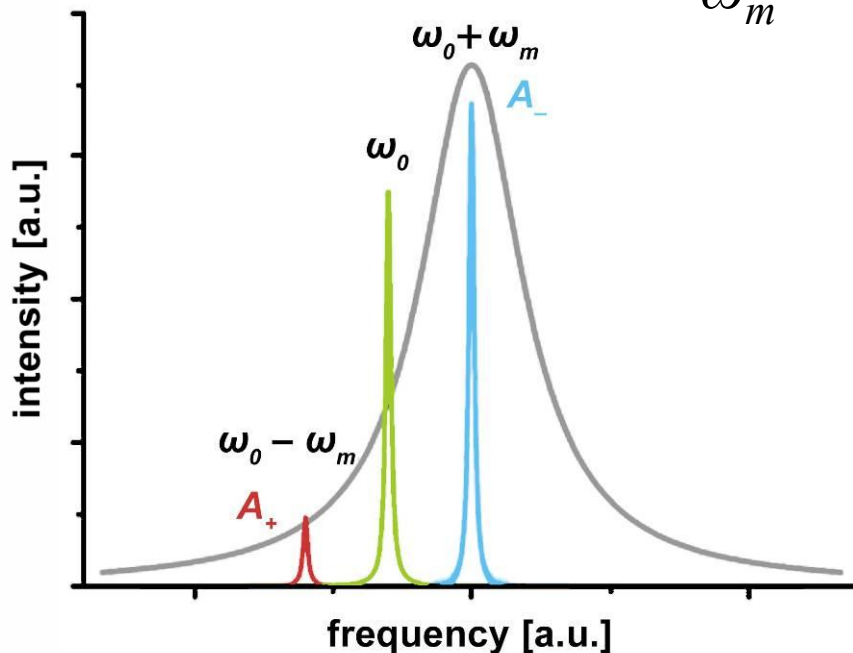
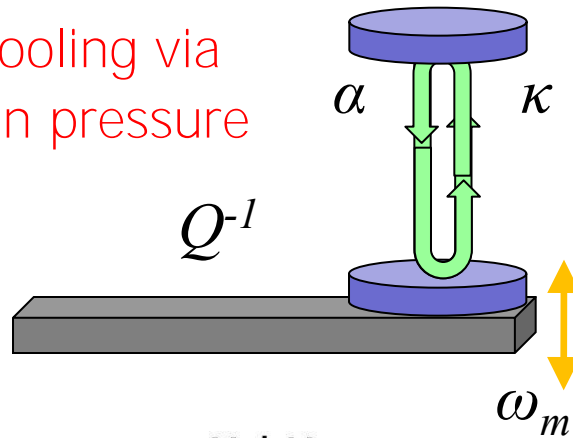


- Dissipation shows no dependence on auxiliary beam position

Cavity-Assisted Optomechanical Cooling



Laser-cooling via radiation pressure



Requirements

- resolved-sideband regime ($\kappa < \omega_m$)
- absence of optical absorption
- shot-noise limited optical pump
- weak coupling to environment
 - cryogenic cavity (mK temp.)
 - large Q (reduce dissipation)

To achieve full quantum control:

$$k_B T / \hbar Q \ll \kappa \ll \omega_m, g_0 \alpha$$

zero entropy
mechanics

strong
coupling